

# VUV Photons and Synergistic Roughening Mechanisms of 193 nm Photoresist in Inductively Coupled Plasmas

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February 10, 2010 – NCCAVS – San Jose

### Changes in Technology & Materials Introduce New Problems in Pattern Transfer: Degradation of 193 nm Photoresists

Key Changes in Photolithography: Wavelength Polymer Chemistry (193 nm PR) Key Changes in Pattern Transfer: Plasma (Dry) Etching



Negeshi, N. et al. J. Vac. Sci. and Technol. 23(1). 2005.





Morimoto, M. Hitachi



Nest, D. Experimental Beam System Studies of Plasma-Polymer Interactions. UC Berkeley. 2009.

### Transistor Leakage Current Increases as PR Line Roughening Increases and Device Dimensions Shrink





Morimoto, M. Hitachi

PR Roughness does NOT scale with feature size



22 nm node: 1.4 nm LWR

Kim, H-W., et al. IEEE Transactions on Electron Devices. 51 (12) 2004.

### 193 nm PR Degradation Depends on Synergy between Vacuum Ultraviolet Photons and High Energy Ions



What Plasma Process Control Parameters affect the Degradation of 193 nm PR caused by VUV Photon & Ion Bombarding Synergy?

- Process blanket 193 nm PR samples in an inductively coupled plasma (ICP).
  - Exposure Time (Fluence of Species)
  - Substrate Temperature
  - Ion Energy



- Improve understanding of the roughening/degradation mechanism of 193 nm PR.
- Correlate roughening observed in blanket samples to patterned samples.

# Ar Inductively Coupled Plasma Diagnostics & Sample Exposure Method

#### ICP Chamber: Top-Down View



# VUV Characterization of Ar ICP determines Processing Conditions

110 W Ar Plasma VUV spectra



# Post Processing Analysis Techniques



# Plasma Induced Smoothing of 193 nm PR (Plasma "Cures")

Plasma "Cure": VUV + Low Energy Ions



E. Pargon et al., Appl. Phys. Letters 94, 3 (2009).
E. Pargon et al., J. Appl. Phys. 105, 11 (2009).
A. Bazin et al., in SPIE, edited by C. L. Henderson (SPIE, 2008), p. 8.

# Plasma Cures: 193 nm PR Bulk Modifications due to C=O and C-O-C Photoabsorption

#### 193 nm PR FTIR Spectra



Titus, M. J. et al. J. Phys. D. Applied Phys., 42, 2009.

# 193 nm PR Remains Smooth with Plasma "Cure" Conditions

#### "Plasma Cure" & VUV Exposure







Bulk Modifications and Changes in Mechanical Properties Correlate with the Smoothing of 193 nm PR



FIG. 13. (Color online) Glass transition temperature  $T_g$  before and after Ar and HBr cure plasma treatments determined by DMAs.

# VUV & Ion Synergy Results in both Physical & Chemical Modifications

#### 193 nm PR FTIR Spectra



# VUV & Ion Synergy Enhances Roughening of 193 nm PR

#### ICP System



0.0 nm

#### Vacuum Beam System

 1.1 x 10<sup>16</sup> cm<sup>-2</sup>
 5.7 x 10<sup>16</sup> cm<sup>-2</sup>
 2.3 x 10<sup>17</sup> cm<sup>-2</sup>
 6.8 x 10<sup>17</sup> cm<sup>-2</sup>

 0.50 nm
 0.57 nm
 2.26 nm
 6.8 x 10<sup>17</sup> cm<sup>-2</sup>

 200 nm
 Image: Constant of the second s

# Threshold Energy for PR Roughening and Formation of a Dehyrogenated (Graphitized) Layer



## PR Roughening is Attributed to Compressive Stress Generated by Bombarding Ions





FIG. 5. Variation of the mass density,  $sp^3$  fraction, and intrinsic stress of ta-C:H as a function of ion energy per C atom. The energy per C atom is 46% of the original  $C_2H_2^+$  ion energy. Also shown is a fit of Eq. (15) to the density.

Weiler, M., et al. Phys. Rev. B., 53 (3), 1996.

# Substrate Temperature Enhances193 nm PR Roughening



# Substrate Temperature Enhances193 nm PR Roughening





0.0 nm

### Conclusions Drawn from Blanket PR Studies



### Does the Mechanism Describing the Roughening of Blanket Samples Apply to Patterned Samples?



S. Engelmann, UMD





LER

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Patterned Samples (Lam Research) Processed in Ar ICP: LWR Measurements Compared to RMS Roughness













Roughening of 193 nm PR in Plasmas due to VUV Photon and Ion Synergy is Established and Leads the way to Understanding Roughening of Patterned Features



Negeshi, N. et al. J. Vac. Sci. and Technol. 23(1). 2005.



Engelmann, S. UMD



Vacuum Beam System Synergy: VUV, Ions & Temperature



#### Simple Plasma: VUV & Ion Synergy





# Acknowledgements

## Funding & Collaboration:

- IMPACT program through the University of California Discovery Research Grant
- National Science Foundation: Award Nos. DMR-0406120 and DMR-0705953
- NERT & GOALI
- Rohm & Haas
- Lam Research: Eric Hudson, Yoko Yamaguchi
- Professor Oehrlein, University of Maryland
- Professor Segalman, University of California, Berkeley